

In re: Kong et al.
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a second susceptor portion formed from graphite coated with silicon carbide, said second susceptor portion facing said substrate-receiving surface and spaced from said substrate-receiving surface, said spacing being sufficiently large to permit the flow of gases therebetween for epitaxial growth on a substrate on said surface, while small enough for said second susceptor to heat the exposed face of a substrate to substantially the same temperature as said first susceptor portion heats the face of a substrate that is in direct contact with said substrate-receiving surface.

Please amend Claim 21 as follows:

21. (Amended) A chemical vapor deposition system comprising:

a reactor vessel formed of a material substantially transparent to electromagnetic radiation;

a gas supply system in fluid communication with said reactor vessel;

a source of electromagnetic radiation external to said reaction vessel; and

a susceptor within said reaction vessel, and formed of a material that is thermally responsive to electromagnetic radiation, said susceptor comprising,

a first susceptor portion formed from graphite coated with silicon carbide and including a surface for receiving a semiconductor substrate wafer thereon; and

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a second susceptor portion formed from graphite coated with silicon carbide, said second susceptor portion facing said substrate-receiving surface and spaced from said substrate-receiving surface, said spacing being sufficiently large to permit the flow of gases therebetween for epitaxial growth on a substrate on said surface, while small enough for said second susceptor to heat the exposed face of a substrate to substantially the same temperature as said first susceptor portion heats the face of a substrate that is in direct contact with said substrate-receiving surface.